

Leonis Ka-band MMIC

LE-Ka1320302

GaAs PHEMT MMIC LOW NOISE AMPLIFIER 17-21GHz & 27-31GHz

Overview

LE-Ka1320302 is a 3-stage MMIC low noise amplifier that covers frequencies from 17GHz to 21GHz and from 27GHz to 31GHz. The LE-Ka1320302 provides up to 20dB of stable gain, with a noise figure of 2.5dB from a 4V supply voltage and 41mA current. By incorporating a self-biased configuration LE-Ka1320302 provides enhanced temperature stability with no need for a negative supply voltage.

The MMIC is fully passivated for additional protection and has all bond pads and backside gold plated. The LE-Ka1320302 MMIC is compatible with precision die attach methods, as well as thermo-compression and thermosonic wire bonding, making it ideal for MCM and hybrid microcircuit applications. All data shown is measured with the chip in a 50 Ohm environment, with 100pF decoupling capacitors on all DC connections and is contacted using RF probes.

Features

- 17 – 21GHz & 27-31GHz
- 20dB Gain
- 2.5dB Noise Figure
- Unconditionally Stable
- No negative DC supply requirement

Applications

- High Speed Data Communications
- Space Communications
- IOT
- Security



No licence is granted under any patent or any patent rights of Arralis. Information furnished by Arralis is believed to be accurate. No responsibility is assumed by Arralis for its use, nor for any infringements on the rights of other parties that may result for the use of the information herein. All specification are subject to change without notice



Specification Overview

Parameter	Min.	Typ.	Max.	Units
Frequency	17		21	GHz
Gain	21.6	22.5		dB
Input Return Loss	10	20		dB
Output Return Loss	5.5	8		dB
Noise Figure		2.5	3.2	dB
Frequency	27		31	GHz
Gain	20	24		dB
Input Return Loss	6	7		dB
Output Return Loss	8	10		dB
Noise Figure		2.5	3.5	dB
Drain Voltage		4		V
Current		41		mA

Notes

The tests indicated have all been performed with 100pF de-coupling capacitors on all bias pads. All tests are carried out at 25°C.

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage	6V
Drain Current	132mA
RF Input Power	7dBm
Storage Temperature	-65°C to +150°C
Channel Temperature	+150°C
Operating Temperature	-40°C to +85°C



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features proprietary protection circuitry, damage may occur on devices subjected to ESD. Proper ESD precautions should be taken to avoid performance degradation or loss of functionality.



Measured Performance Data

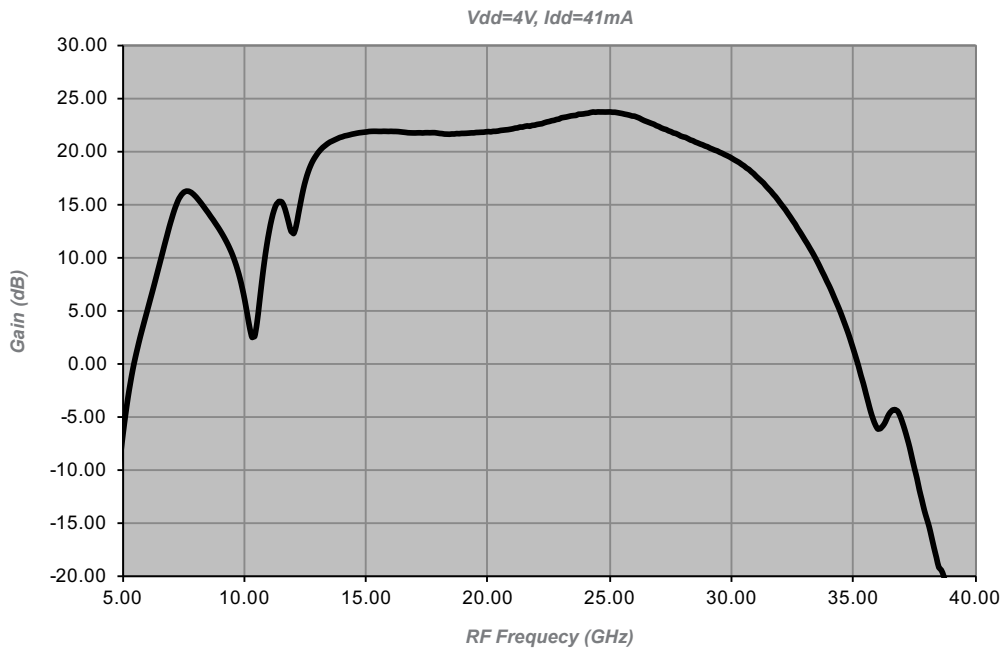


Figure 1
LE-Ka 1320302
Gain

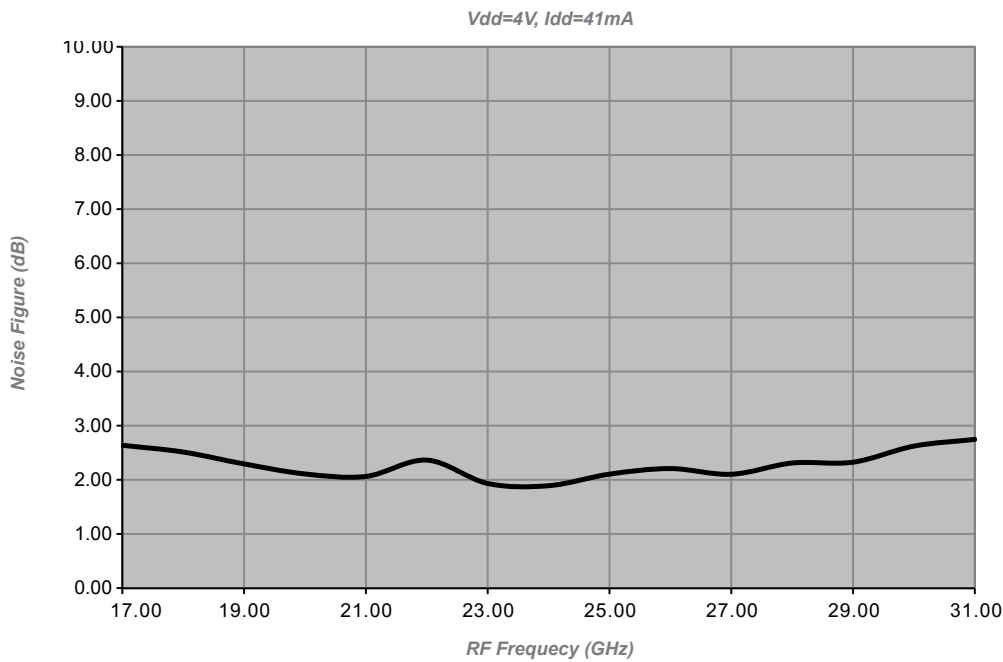


Figure 2
LE-Ka 1320302
Noise Figure



Measured Performance Data

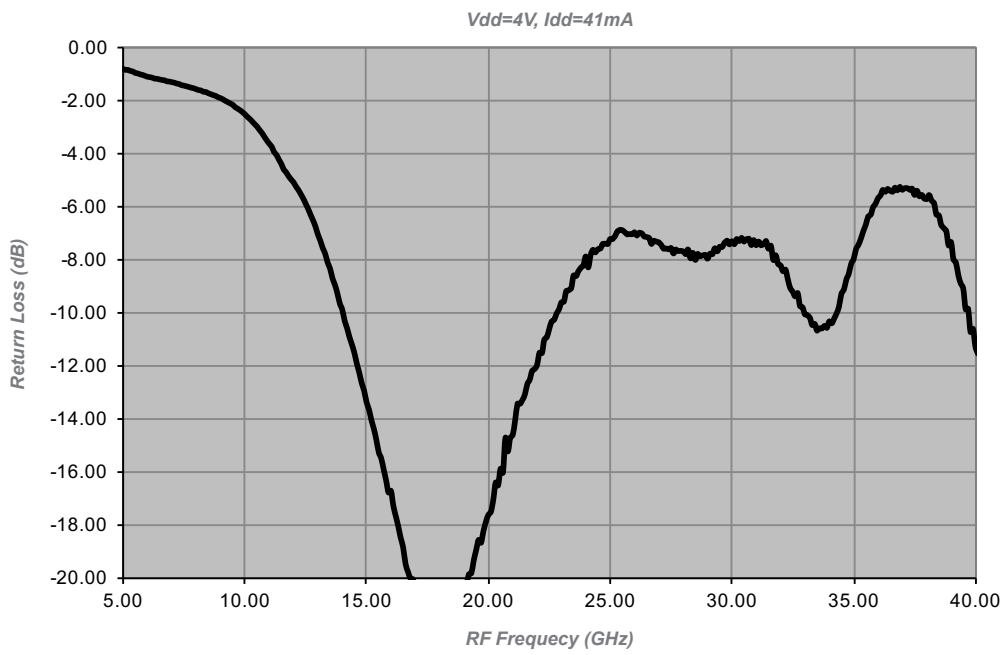


Figure 3
LE-Ka 1320302
Input Return Loss

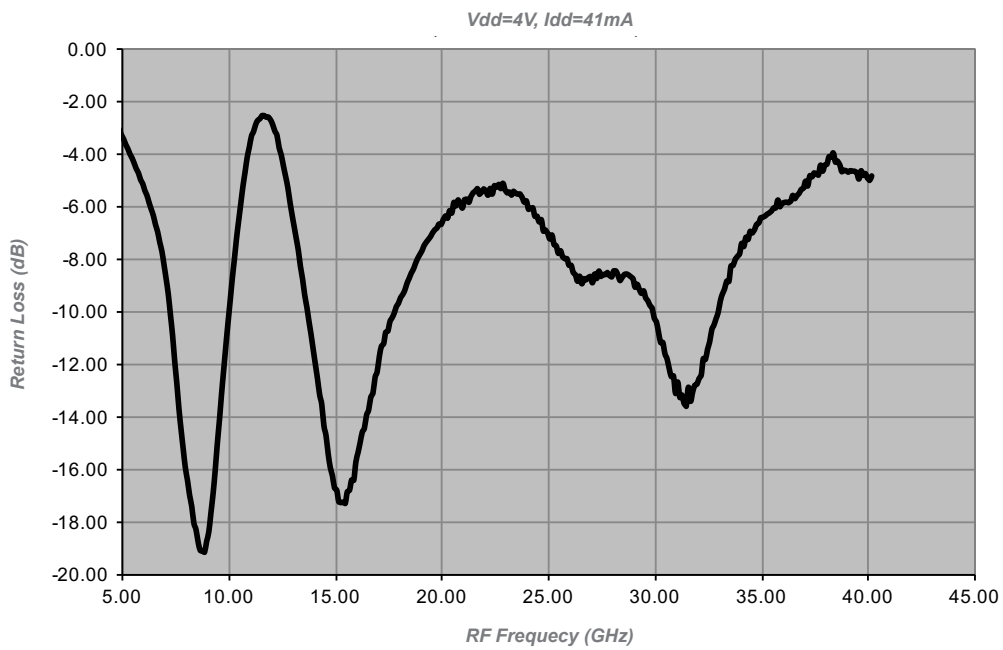
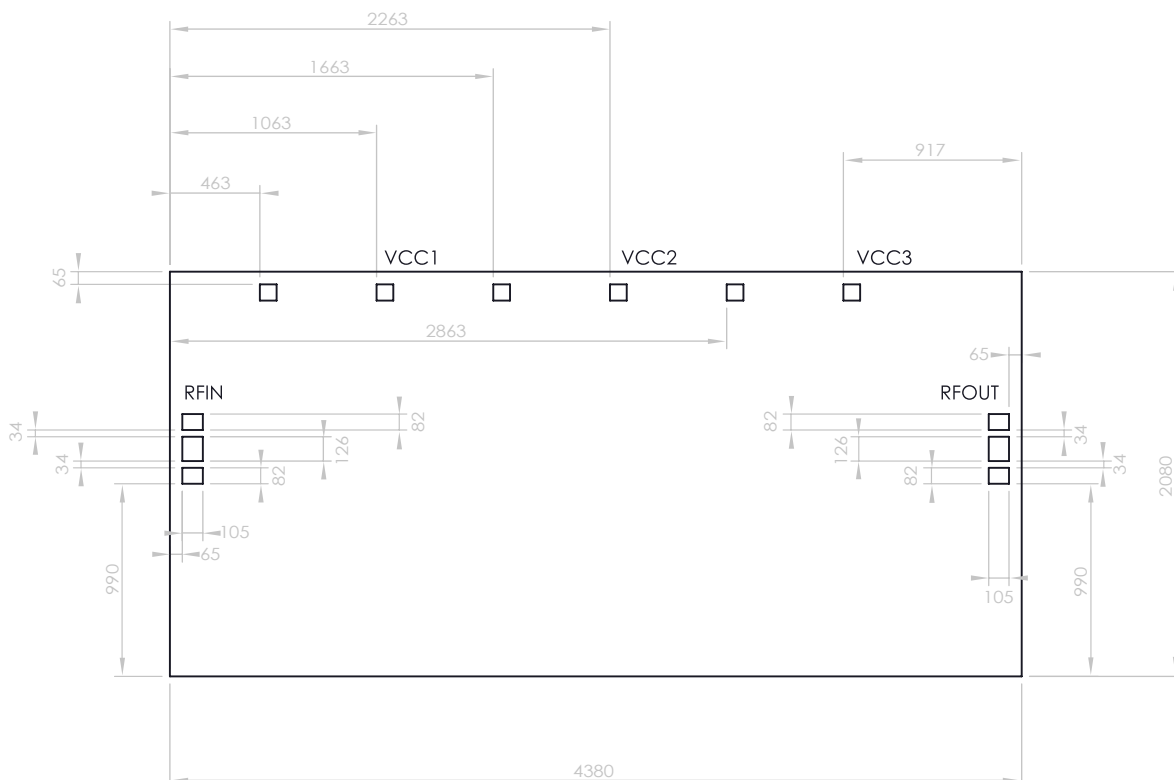


Figure 4
LE-Ka 1320302
Output Return Loss



Outline Drawing



Notes

1. All dimensions are in μm .
2. Typical dc bond pads are $80\mu\text{m}$ square.
3. RF bond pads are $105 \times 120\mu\text{m}$ square.
4. All pads have gold metalisation.
5. Gold backside metalisation.
6. Backside metal is ground.
7. Connections are not required for unlabelled bond pads.
8. Die thickness is $100\mu\text{m}$

Die Packing Information

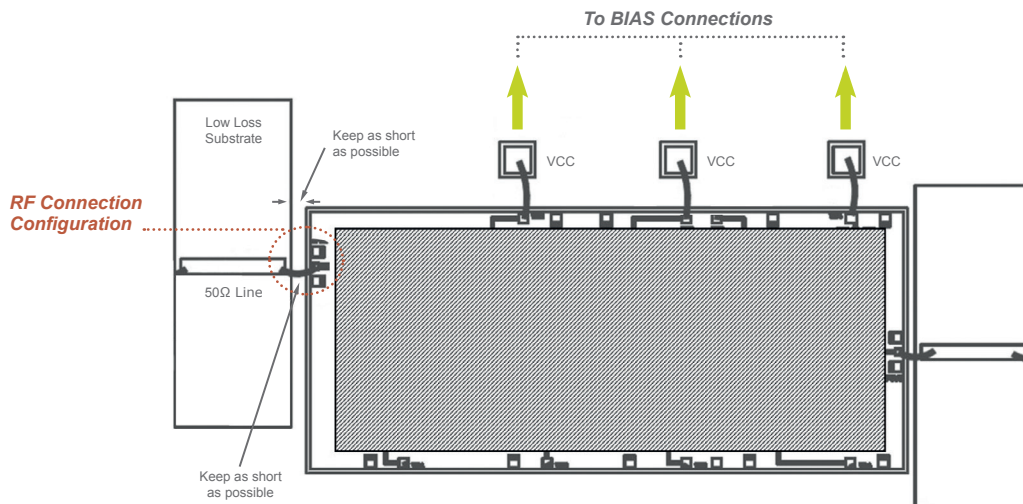
All die are delivered using gel-paks unless otherwise requested.



Pad Descriptions

Name	Description
RFIN	Input RF pad. This pad is ac coupled.
RFOUT	Output RF pad. This pad is ac coupled.
VCCx	Drain bias pad for stage x
BOTTOM	The die backside must be connected to RF/dc ground.

Connection Configurations



(Not actual die – these rules are applied to all MMICs unless otherwise stated)



General Notes on Assembly

Die should be mounted on conductive material such as gold-plated metal to provide a good ground and suitable heat sink, if necessary.

1. Attaching the die using Au/Sn preforms is preferable. The Eutectic melt for Au/Sn occurs at approximately 280°C so the die (plus mount and preform) is initially heated up to 180°C and then it is heated for approximately 10 seconds to 280°C using a nitrogen heat gun. The device will survive 10 seconds at this temperature. The static breakdown for GaAs devices is approximately 330°C.
2. Pure, dry Nitrogen should be used as the heat source.
3. If the devices cannot be lifted/ placed by a vacuum device, then ESD die-lifting tweezers are preferable.
4. Supply lines should be decoupled with 100pF capacitors. Larger planar capacitors could be used if available.
5. Aluminium wire must not be used.



©2017 Arralis Ltd. All rights reserved. Trademarks and registered trademarks are the property of their respective owners.

Arralis, Tierney Building UL, Castletroy, Limerick V94NYD3, Ireland (IRL). Tel: +353 61 748 264

Arralis, ECIT, Northern Ireland Science Park, Queen's Road, Queen's Island, Belfast BT3 9DT, United Kingdom (UK). Tel: +44 28 9045 4021

Email: info@arralis.com **Web:** www.arralis.com

